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SSU1N50B **520V N-Channel MOSFET**

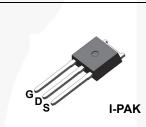
General Description

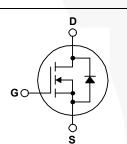
These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switch mode power supplies, power factor correction and electronic lamp ballasts based on half bridge.

Features

- 1.3A, 520V, R_{DS(on)} = 5.3Ω @ V_{GS} = 10 V
 Low Gate Charge (Typ. 8.3 nC)
- Low Crss (Typ. 5.5 pF) •
- Fast Switching
- 100% Avalanche Tested
- Improved dv/dt Capability





Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter		SSU1N50BTU	Unit	
V _{DSS}	Drain-Source Voltage		520	V	
ID	Drain Current - Continuous (T _C = 25	1.3	A		
	- Continuous (T _C = 10	0.82			
I _{DM}	Drain Current - Pulsed	(Note 1)	5.0	A	
V _{GSS}	Gate-Source Voltage	± 30	V		
E _{AS}	Single Pulsed Avalanche Energy (Note 2		100	mJ	
I _{AR}	Avalanche Current	(Note 1)	1.3	A	
E _{AR}	Repetitive Avalanche Energy	(Note 1)	2.6	mJ	
dv/dt	Peak Diode Recovery dv/dt (Note 3)		5.5	V/ns	
P _D	Power Dissipation ($T_A = 25^{\circ}C$) *		2.5	W	
	Power Dissipation ($T_C = 25^{\circ}C$)	26 W			
	- Derate above 25°C	0.21	W/°C		
T _J , T _{stg}	Operating and Storage Temperature Range		-55 to +150	°C	
TL	Maximum lead temperature for soldering 1/8" from case for 5 seconds	300	°C		

Thermal Characteristics

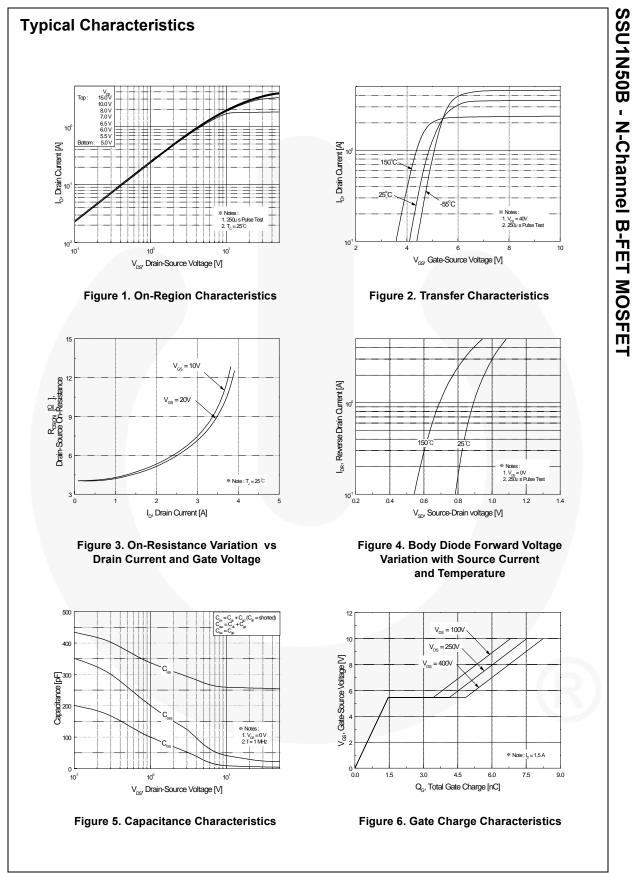
Symbol	Parameter	SSU1N50BTU	Unit °C/W	
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction-to-Case, Max.	4.76		
R_{\thetaJA}	Thermal Resistance, Junction-to-Ambient (*1 in ² Pad of 2-oz Copper), Max	50	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Minimum Pad of 2-oz Copper), Max.	110	°C/W	

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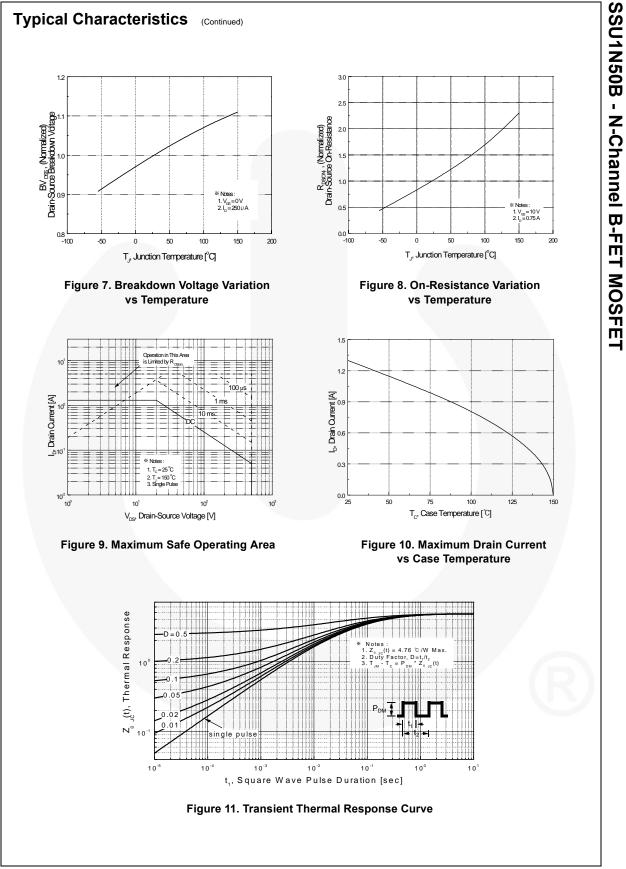
SSU1N50B - N-Channel B-FET MOSFET

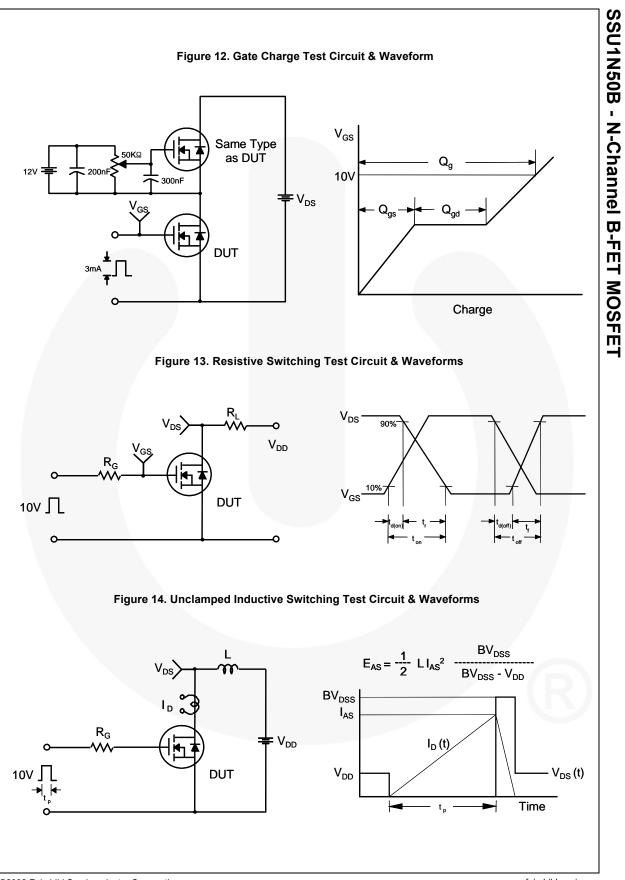
April 2014

Part Nu	mber	er Top Mark		Package Packing Method Reel		Reel	Size	Tape Width		Quantity	
SSU1N50BTU SSU1N50B I-P					4	N/A		70 units			
Electric	cal Cł	naracteristics	T _C = 25°C	cunless ot	herwise noted						
Symbol		Parameter			Test Cor	ditions		Min	Тур	Max	Unit
Off Cha	racter	istics									
BV _{DSS}	Drain-Source Breakdown Voltage			$V_{GS} = 0 V, I_D = 250 \mu A$			520			V	
ΔBV _{DSS} / ΔT _J		eakdown Voltage Temperature			$I_D = 250 \mu\text{A}$, Referenced to 25°C				0.54		V/°C
I _{DSS}				V _{DS} = 520 V, V _{GS} = 0 V					10	μA	
200	Zero Gate Voltage Drain Current			$V_{DS} = 400 \text{ V}, \text{ T}_{C} = 125^{\circ}\text{C}$						100	μΑ
I _{GSSF}	Gate-B	Gate-Body Leakage Current, Forward			V _{GS} = 30 V, V _{DS} = 0 V					100	nA
I _{GSSR}	Gate-B	ody Leakage Current,	Reverse	$V_{GS} = -30 \text{ V}, V_{DS} = 0 \text{ V}$						-100	nA
On Cha	racter	istics									
V _{GS(th)}	Gate T	hreshold Voltage	_	V _{DS} =	V_{GS} , $I_D = 2$	50 μΑ		2.0		4.0	V
R _{DS(on)}		Drain-Source sistance		V _{GS} =	10 V, I _D =).65 A			4.1	5.3	Ω
9 _{FS}	Forwar	d Transconductance	-	V _{DS} =	40 V, I _D = 0	.65 A			1.65		S
Dynam C _{iss}	1	racteristics capacitance	-	V _{DS} =	25 V, V _{GS}	= 0 V.			260	340	pF
C _{oss}	Output	Capacitance			V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz				25	33	pF
C _{rss}	Revers	e Transfer Capacitance	е					5.5	7.2	pF	
Switchi	ng Ch	aracteristics									
t _{d(on)}		n Delay Time		V _	V_{DD} = 250 V, I_D = 1.5 A, R _G = 25 Ω				14	40	ns
t _r	Turn-O	n Rise Time						40	90	ns	
t _{d(off)}	Turn-O	ff Delay Time		NG = 2	10 12				35	80	ns
t _f	Turn-O	ff Fall Time		Ī			(Note 4)		35	80	ns
Qg	Total G	ate Charge		V _{DS} =	400 V, I _D =	1.5 A,			8.3	11	nC
Q _{gs}	Gate-S	ource Charge		V _{GS} =	10 V				1.5		nC
Q _{gd}	Gate-D	rain Charge					(Note 4)		3.4		nC
Drain-S	ource	Diode Characteri	stics ar	nd Max	kimum R	atings					
I _S	-	um Continuous Drain-S				-				1.3	Α
I _{SM}	Maxim	um Pulsed Drain-Sourd	e Diode F						5.0	Α	
V _{SD}		Source Diode Forward			0 V, I _S = 1.	3 A				1.4	V
t _{rr}		e Recovery Time	0	$V_{GS} = 0 \text{ V}, \text{ I}_{S} = 1.5 \text{ A},$			230	-	ns		
Q _{rr}	Revers	e Recovery Charge		$dl_{\rm F} / dt = 100 \text{ A/}\mu\text{s}$				0.94		μC	
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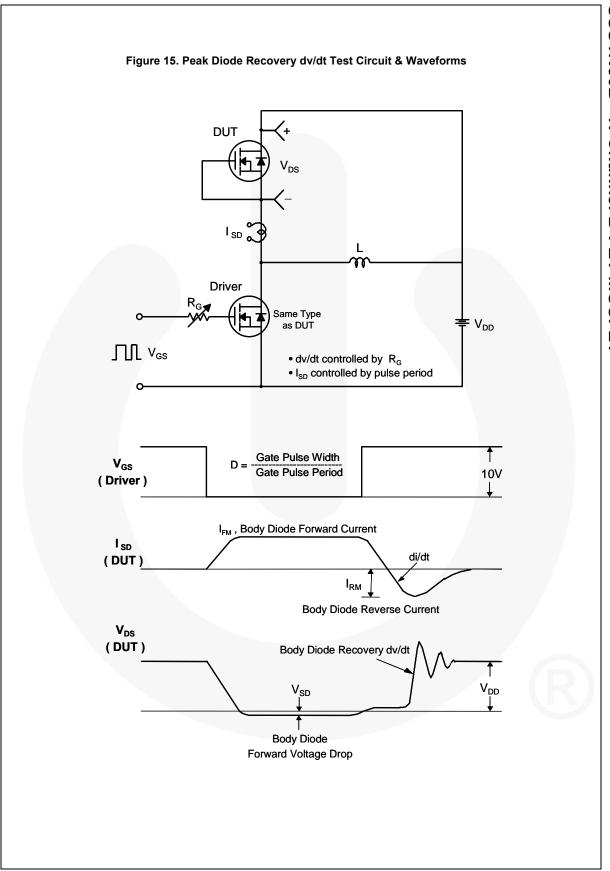


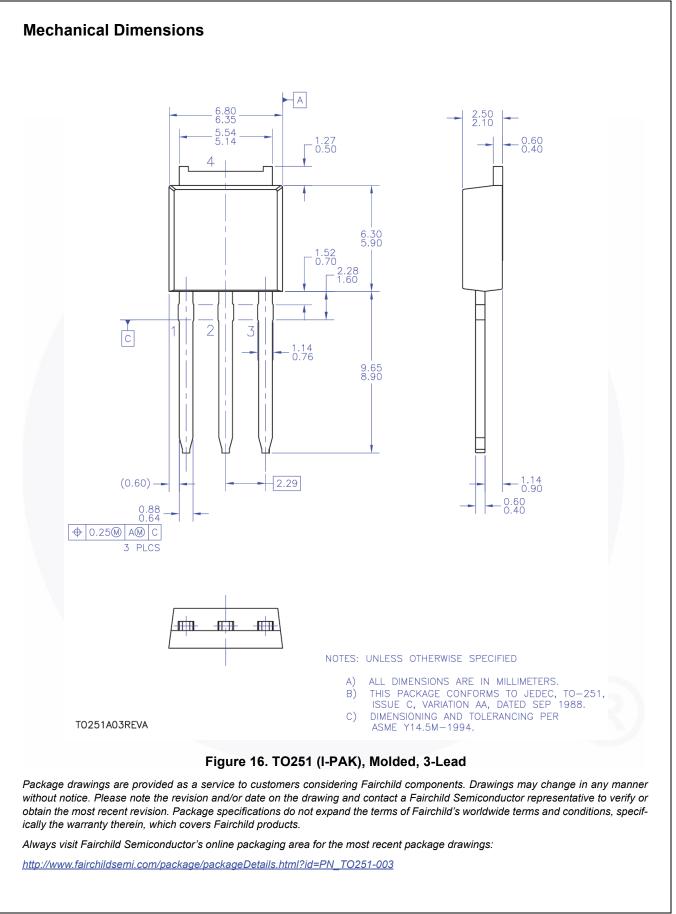
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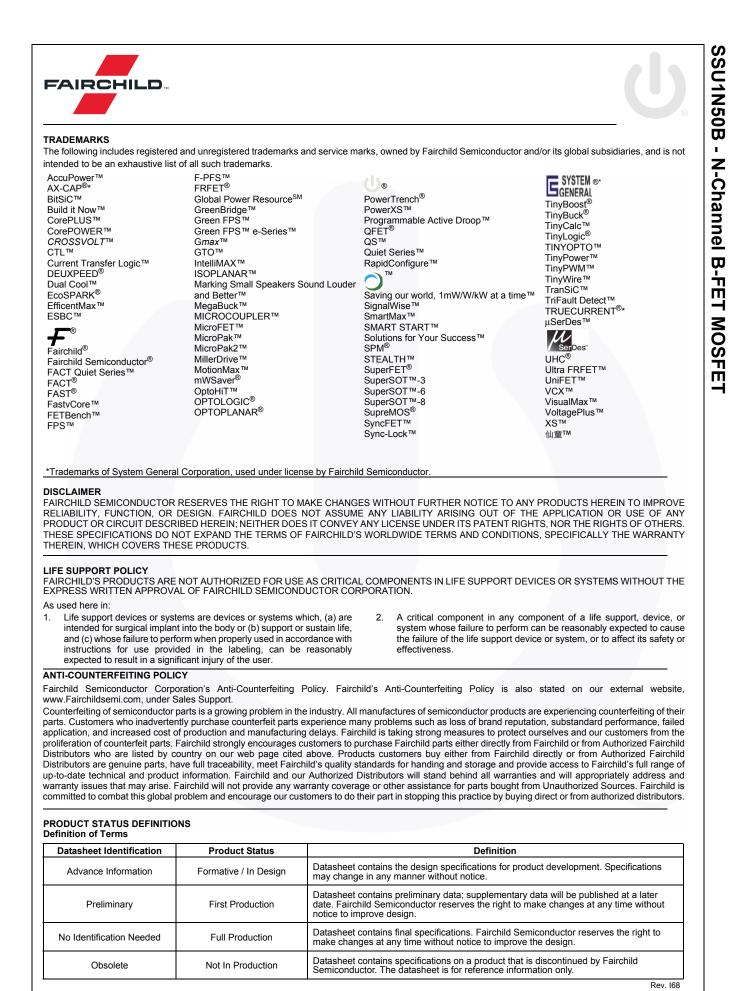




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